

TAIYANGNEWS

ALL ABOUT SOLAR POWER

Solar Technology Conference India 2026

📅 Feb 5-6, 2026 ⌚ 09:30 AM

📍 Hotel Pride Plaza - Aerocity, New Delhi, India

Leadmicro 微导

股票代码 688147

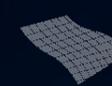
Latest Progress of TBC Equipment Solutions

Baochen LIAO (CTO/Professor)

2026.02.06

江苏微导纳米科技股份有限公司

Jiangsu Leadmicro Nano-Technology Co., Ltd.



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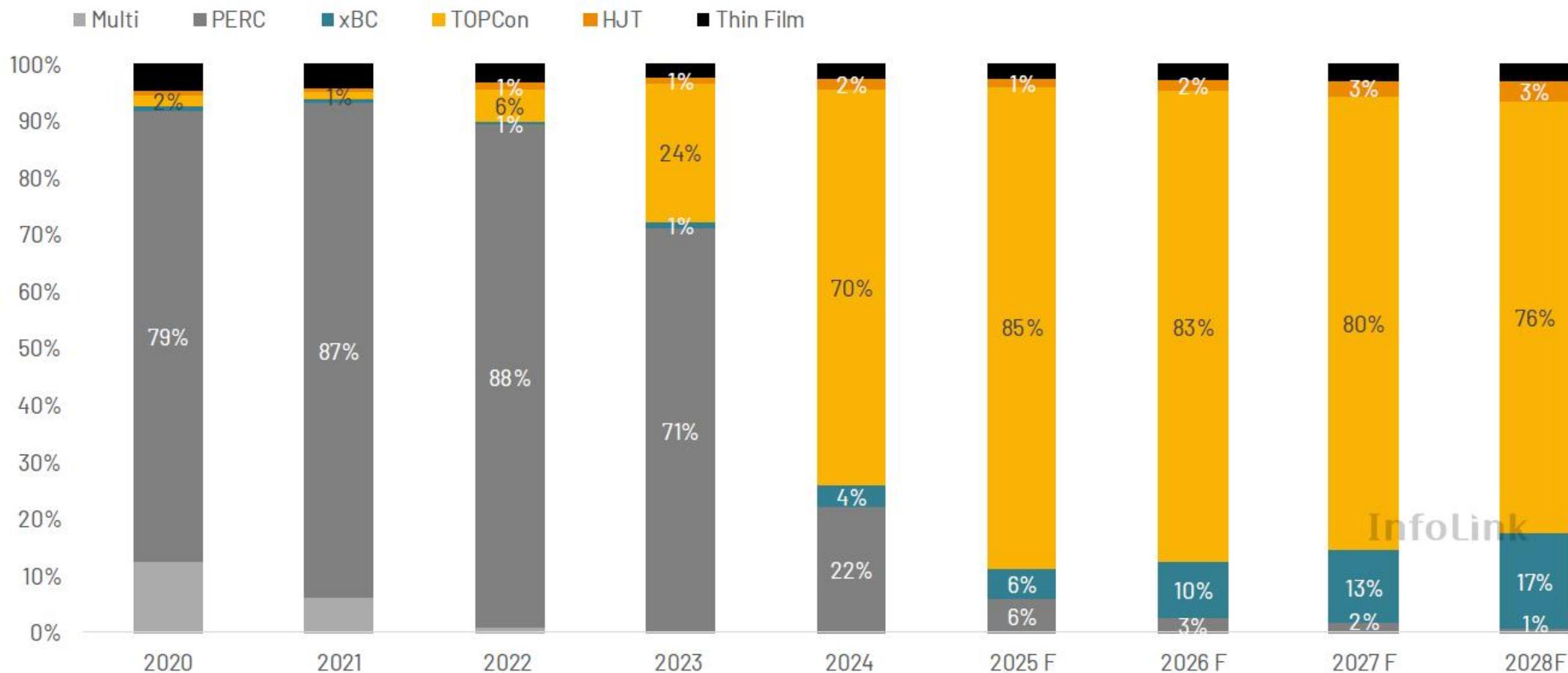
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- Recent Progress of Cell Technologies
- TOPCon to TBC Solutions
- Progress of TBC Equipment Technology
- Company Introduction
- Conclusion

01

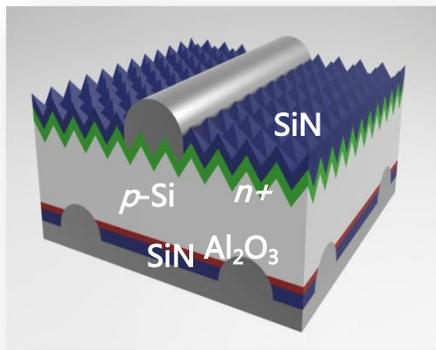
Recent Progress of Cell Technologies

➤ Trend of Cell Technology



PERC Era

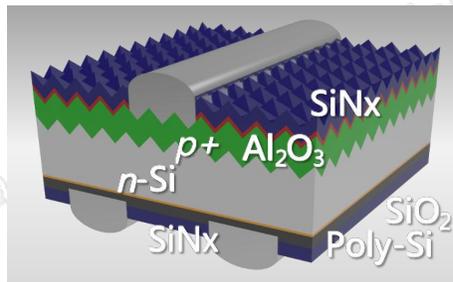
1st Gen KF4600, World first batch ALD with highest throughput, tailored for PERC, Eta. > 23.2%



2016-2019

TOPCon Era

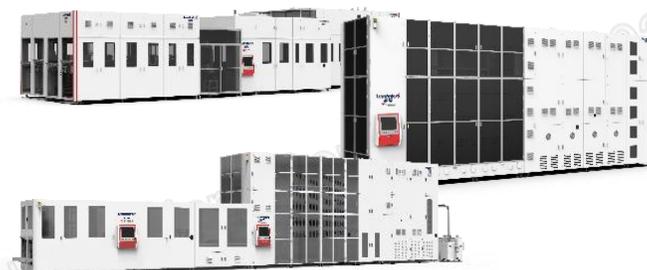
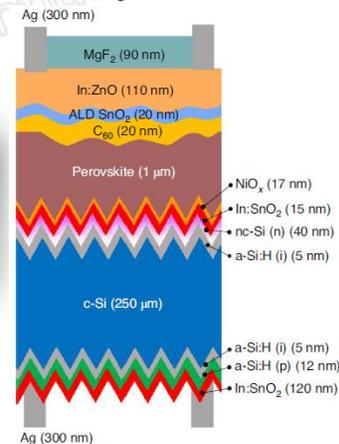
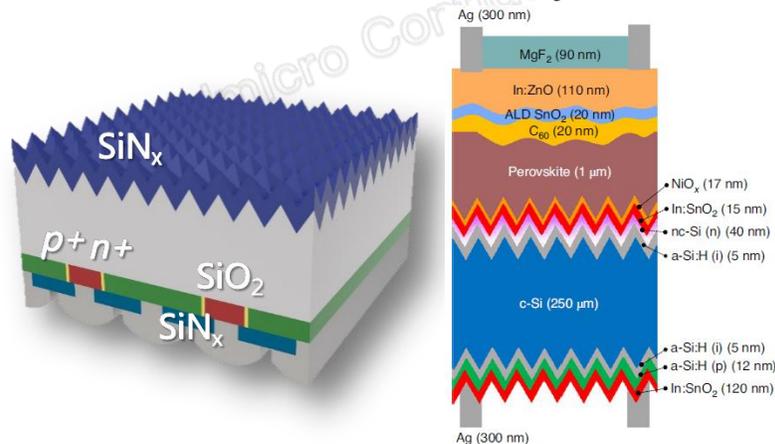
1. Tube ALD breakthrough for TOPCon
2. Pioneer in PE-ToxPoly new tech. dev.
3. PE-TOPCon Turnkey Project 16GW



2019-2024

Future (XBC & Perovskite & Tandem)

1. TOPCon+/TBC: EPD, Laser etc.
2. TBC Turnkey Solutions: PE-ToxPoly(p)
3. Perovskite, Tandem Turnkey Solutions

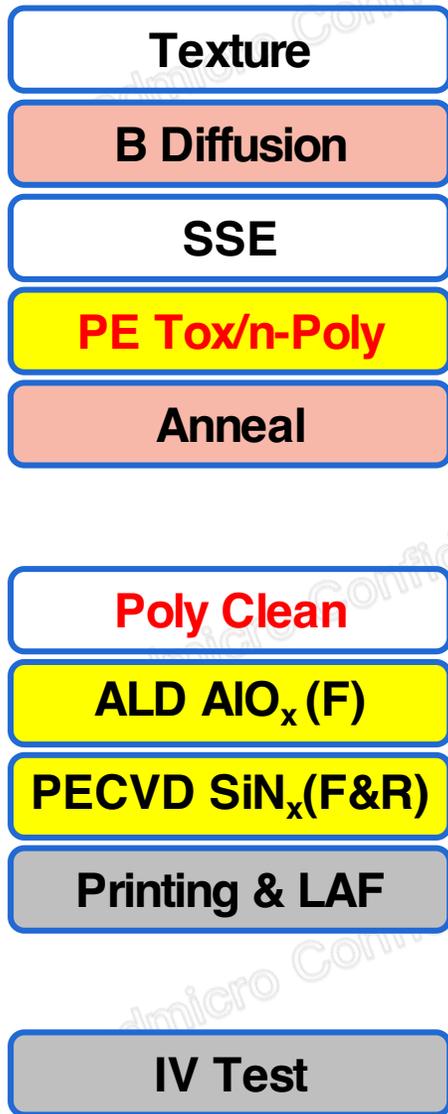


2024 onwards

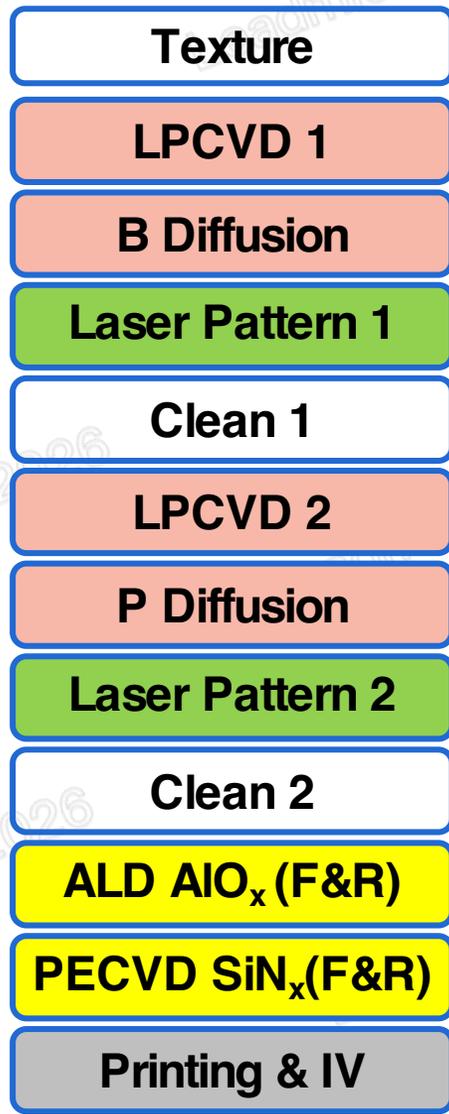
02

TOPCon to TBC Solutions

PE-TOPCon 3.0



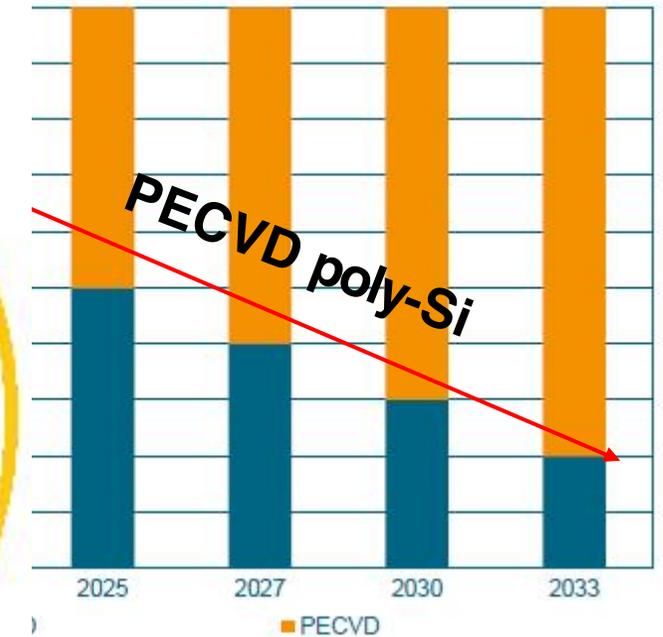
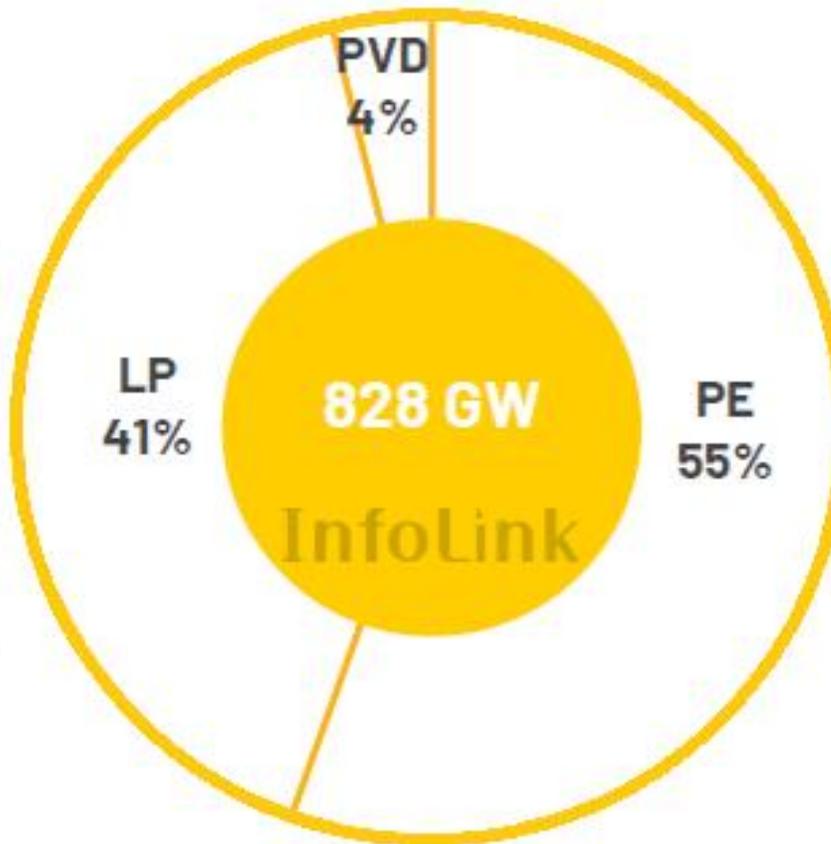
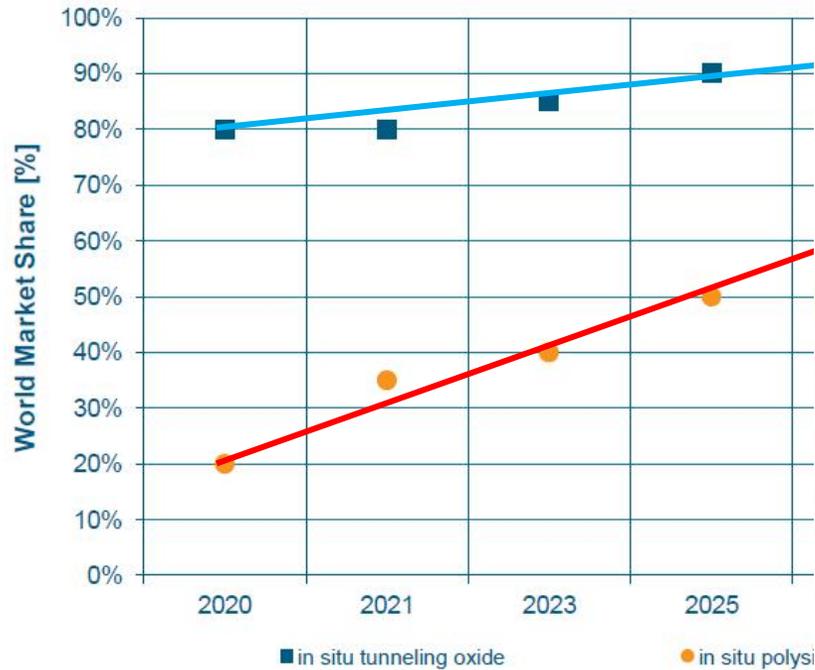
TBC (LP)



TBC (LP+PE)



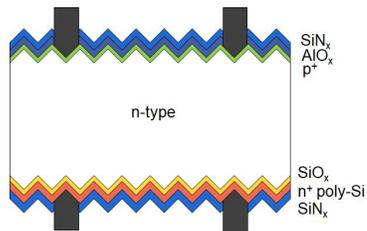
- Tunnel oxide and poly-Si: in-situ
- Poly-Si : LPCVD VS PECVD (~ 80%)



24%

PE-TOPCon 0.0 (Pilot-line)

1. Completed **feasibility pilot-line study**
2. Solved **process & equip. bottlenecks**
3. Eta > 24%

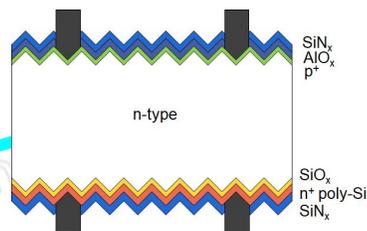


2021.06

26%

PE-TOPCon 1.0 (GW Scale mass-prod. evalu.)

1. Completed **1GW Mass-prod. study**
2. Solved **Yield bottleneck**
3. Eta > 26%, Yield > 97%

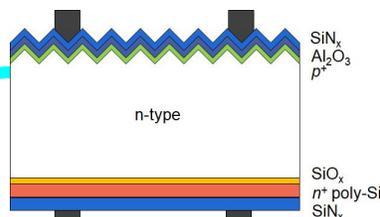


2022.06

26.6%

PE-TOPCon 1.6 (Factory level Mass-prod.)

1. **Factory level expansion**
2. Solved mass-prod. expansion problems.
3. Eta: **rear morphology, anneal opt., screen-printing etc.**

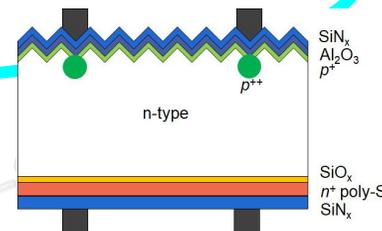


2023.06

26%

PE-TOPCon 2.0 (Mass-prod.)

1. Cost: **2% PH3 → 8% PH3 (~3 times↓)**
2. Eta : **SE, rear opt. polish+paste, Tox+Poly etc.**

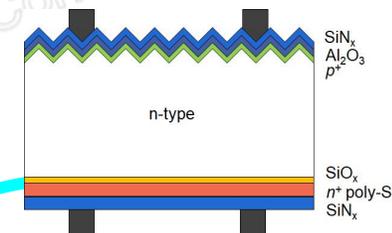


2023.12

> 26%

PE-TOPCon 3.0 (Mass-prod.)

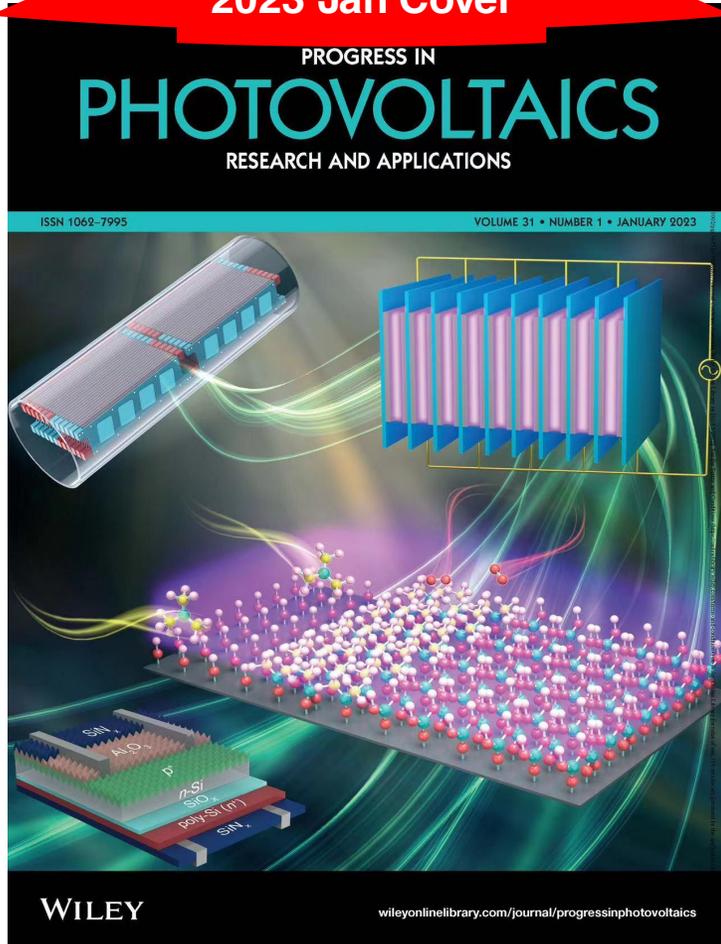
1. **Laser assisted firing**
2. **Front-side opt.**



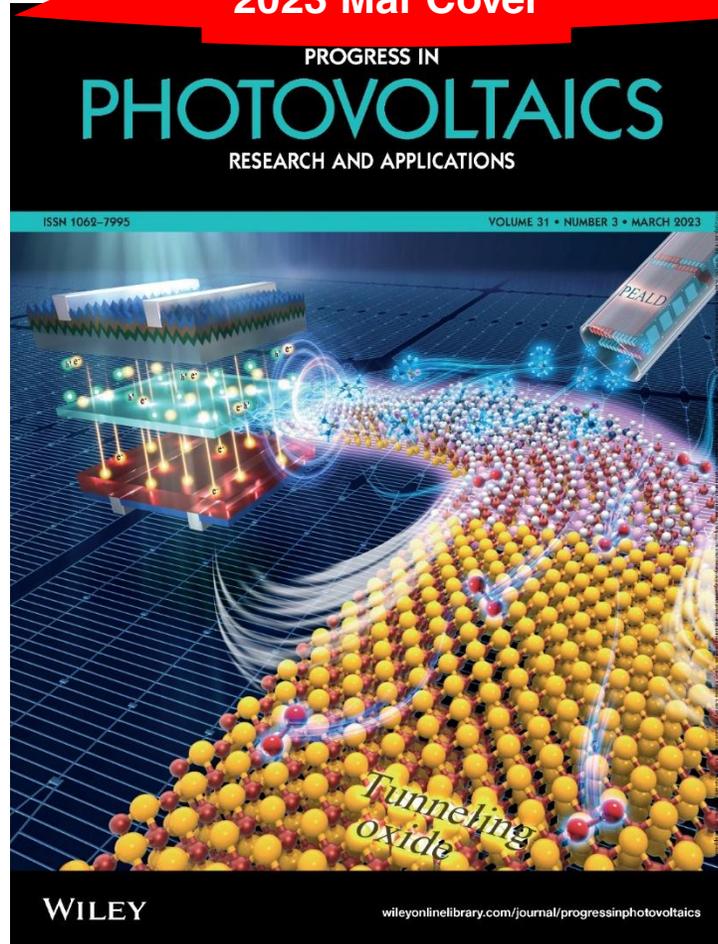
2024.12

- Selected as PIP featured cover twice
- Well recognized internationally (including Europe, US, Latin, Spain, India etc.)

2023 Jan Cover



2023 Mar Cover



pv magazine

SOLAR NEWS

TOPCon solar cell achieves 24.2% efficiency via plasma-assisted atomic layer deposition tech

TOPCON SOLAR CELL ACHIEVES 24.2% EFFICIENCY VIA NEW PLASMA-ASSISTED ATOMIC LAYER DEPOSITION TECH

In Solar News, Sustainability by EISol / 17 October 2022 / Leave a Comment

An international research team has fabricated a tunnel oxide passivated contacts (TOPCon) solar cell through a new technique enabling the control of tunnel oxide deposition at the atomic scale.

The scientists described the proposed method as an innovative tube-type industrial plasma-assisted atomic layer deposition (PEALD) technique. They claimed that it can produce high-quality dense tunnel silicon oxide (SiO₂) films at

monocrystalline PERC solar module

A team of researchers from the Chinese Academy of Sciences (CAS) has developed a new technique for depositing TOPCon solar cells. The team achieved a record efficiency of 24.2% for a TOPCon solar cell.

TECHNOLOGIE

La cellule solaire TOPCon atteint une efficacité de 24,2 % grâce à la nouvelle technologie de dépôt de couche atomique assistée par plasma

Les scientifiques ont décrit la méthode proposée comme une nouvelle technique de dépôt de couche atomique industrielle assistée par plasma (PEALD) de type tunnel. Selon eux, il

peut produire des films d'oxyde de haute qualité, à faible coût et à haut rendement.

Selon les chercheurs, cette méthode de dépôt chimique en phase vapeur permet la fabrication de modules solaires

MERCOM
clean energy insights

TOPCon Solar Cells Achieve 22.8% Efficiency With Plasma-Aided Atomic Layer Deposition

The tunnel oxide deposition thickness was controlled at the atomic scale for higher efficiency

TAIYANGNEWS

ALL ABOUT SOLAR POWER

Interview – Baochen LIAO, Leadmicro

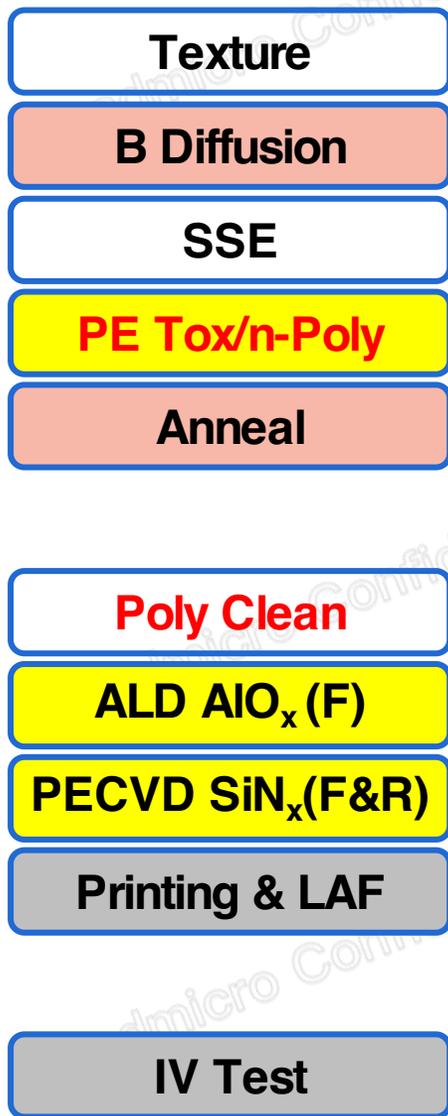
Single sided process with PECVD is the key enabler for TOPCon

in method wherein they ultrathin silicon oxide layer of -Si (n⁺) interface.

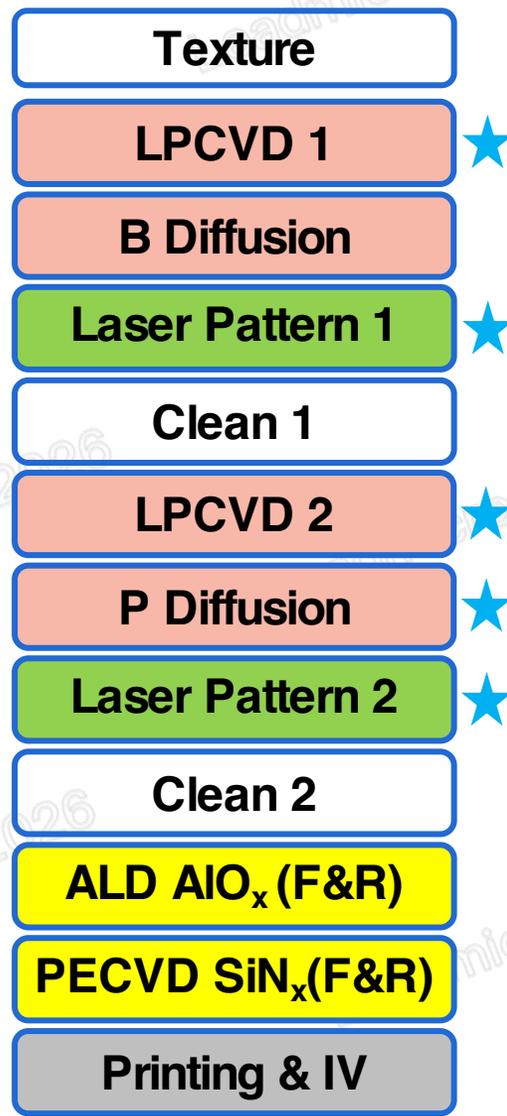
the tunnel oxide thickness at the atomic scale for

Highly Confidential & Proprietary

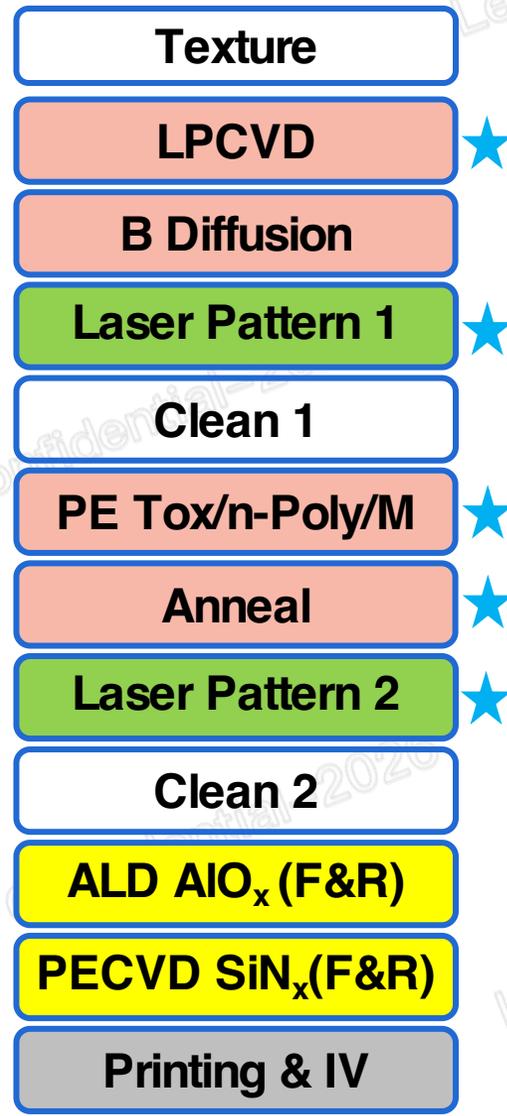
PE-TOPCon 3.0



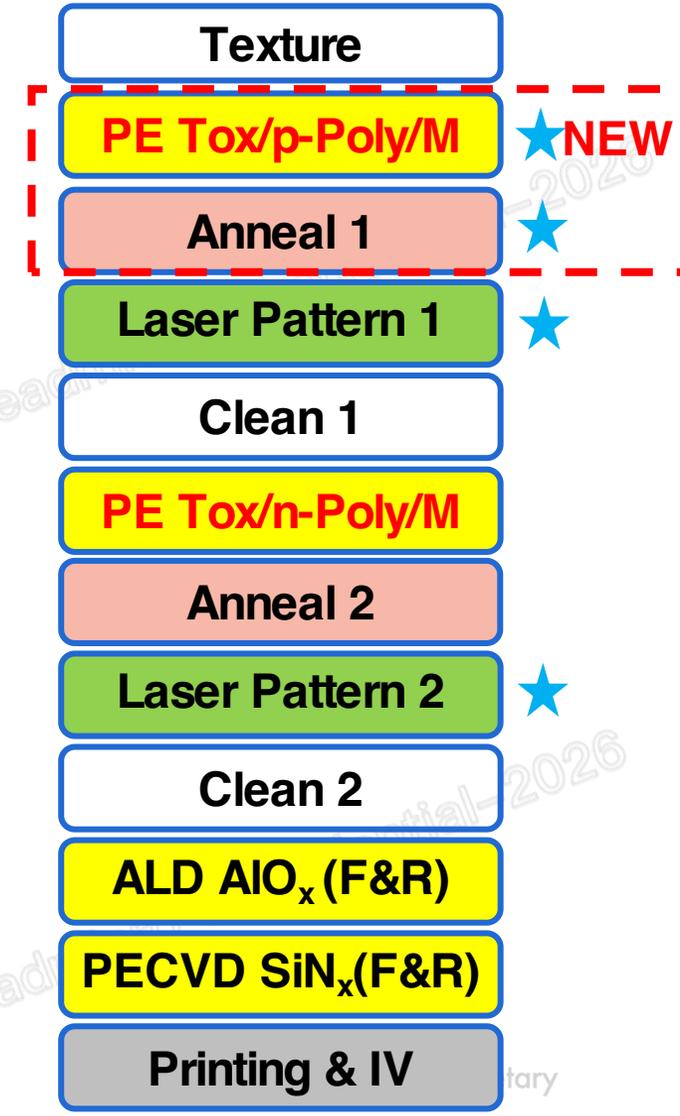
TBC (LP)



TBC (LP+PE)



TBC (PE)

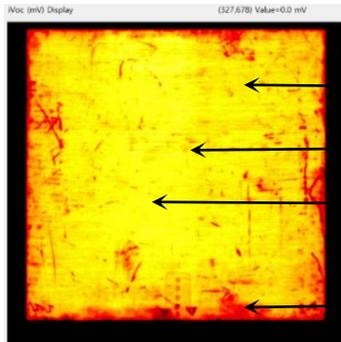
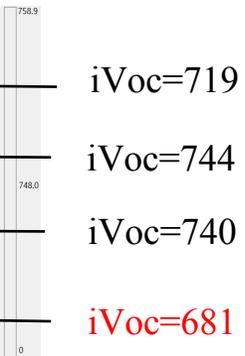
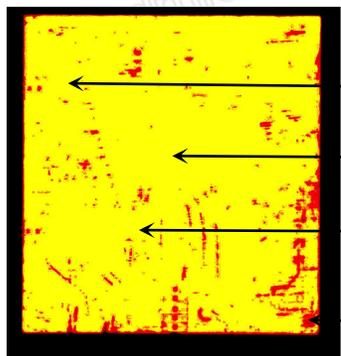


PECVD in-situ p-Poly Industrialization Breakthrough

LPCVD

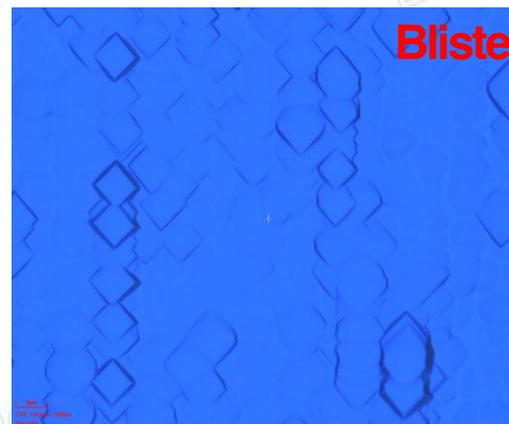
Passivation

PECVD

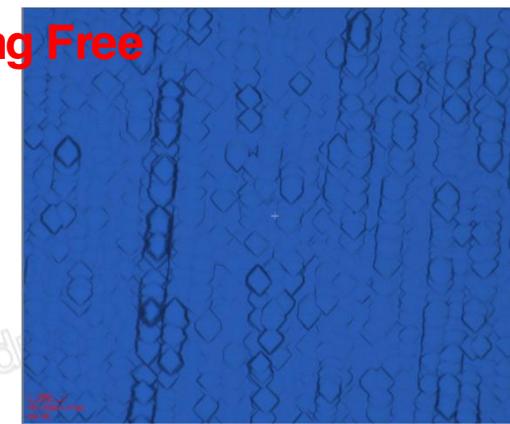


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iVoc=744
iVoc=740
iVoc=681

iVoc=728
iVoc=748
iVoc=746
iVoc=678

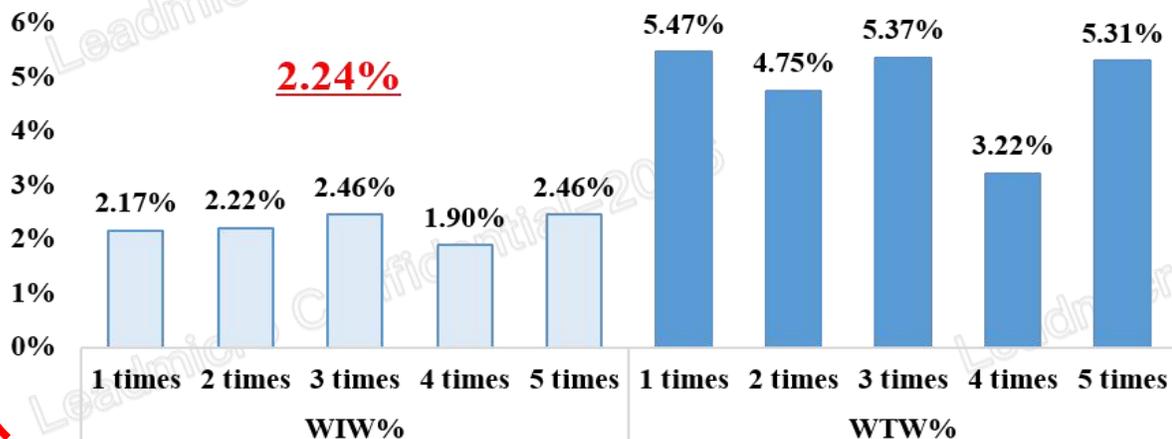


Blistering Free

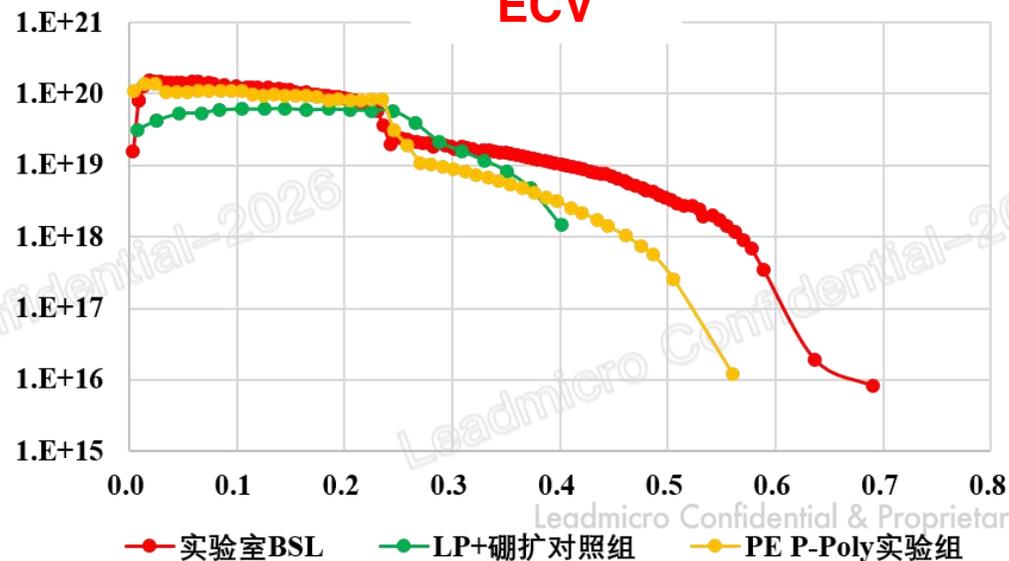


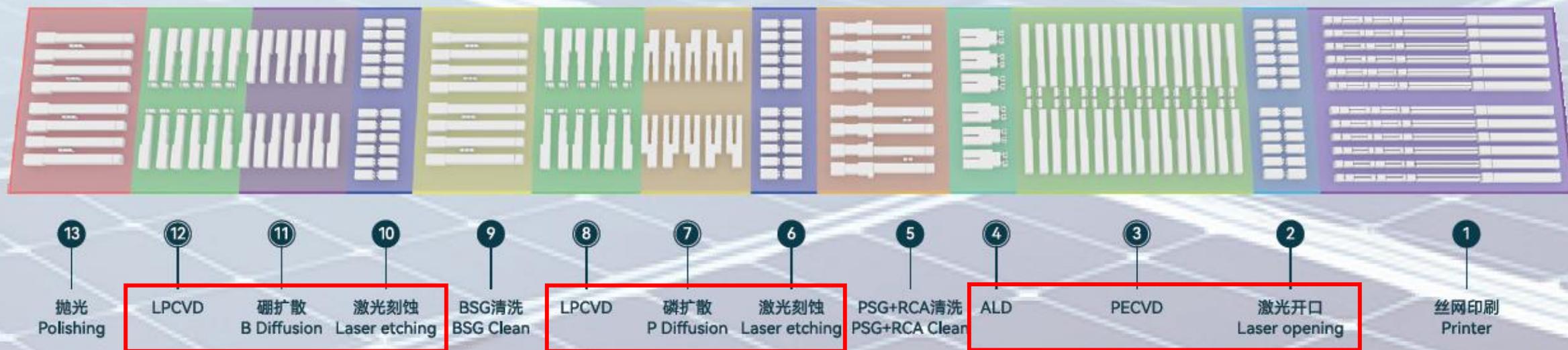
Uniformity

4.82%



ECV

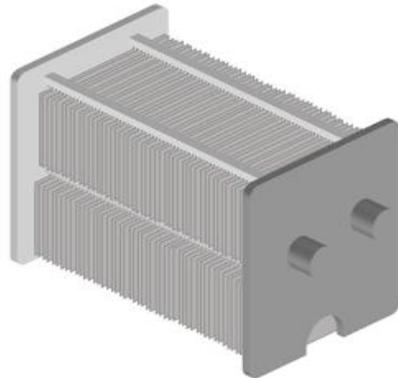
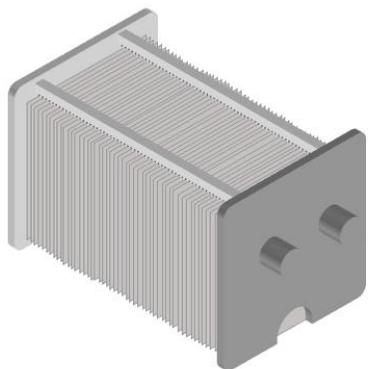
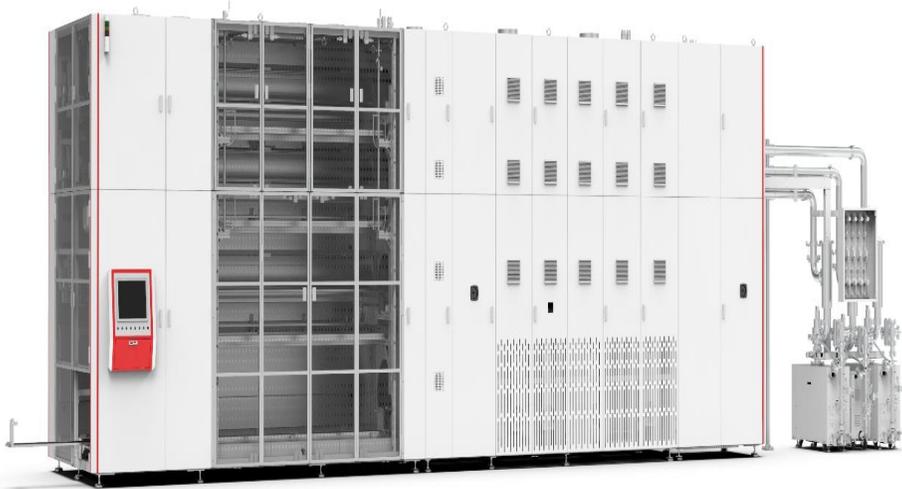




3.1

Technical Progress of LPCVD

XH10000LP Equipment Adv.



**Capacity
High**

182*106:
6760 pcs/tube

**Performance
Excellent**

**Unique Temp. and
Gas flow design**

Uniformity: 3%3%3%

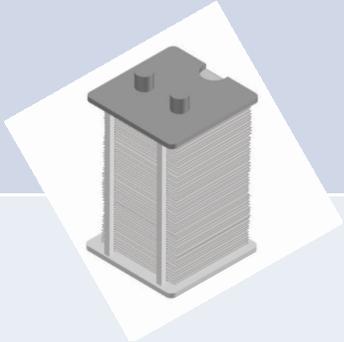
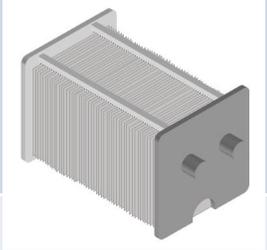
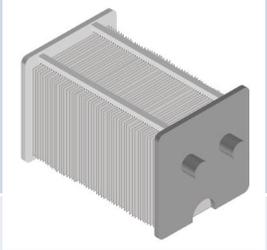
**Loading
Method**

**Like-PE
Compatible with
half cell design**

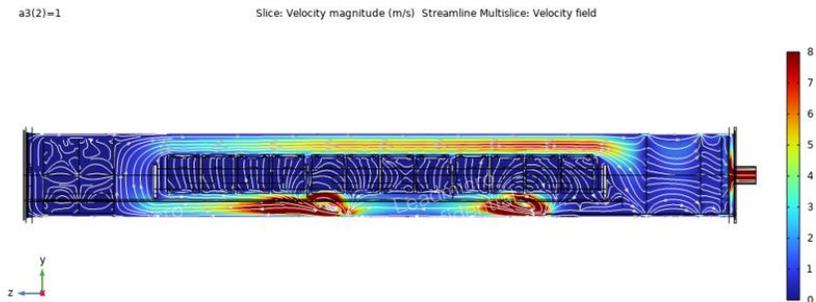
**Easy Maint.
Uptime High**

**Double-paddle design
Tailored design for high
throughput**

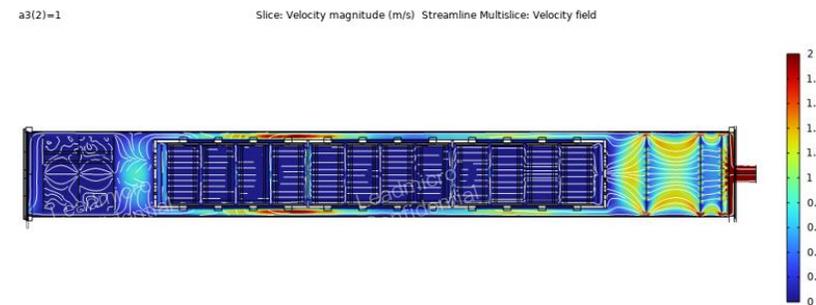
Leadmicro Confidential & Proprietary

Loading Methods	Horizontal (2 nd Gen.)	Like-PE (3 rd Gen.)
		
Advantages	<ol style="list-style-type: none"> 1. Minimal dark edge 	 <ol style="list-style-type: none"> 1. No bending 2. No wafer sticking issue caused broken edges and corner damage 3. No hidden cracks 4. Better film uniformity 5. Lower chemical consumption (COO)
Dis-advantages	<ol style="list-style-type: none"> 1. Wafer bending 2. Wafer sticking caused broken edges and corner damage 3. Hidden cracks 4. Film uniformity issue & High COO 	<ol style="list-style-type: none"> 1. Dark edges (PL)
TOP 3 defects	<ol style="list-style-type: none"> 1. Dark edges: ~ 0.3% 2. Dark spots: ~ 0.3% 3. Scratch: ~ 0.2% 	<ol style="list-style-type: none"> 1. Hidden cracks: 2% - 3% 2. Dirt: ~ 0.2% 3. Dark spots: 0.6% - 0.8%
Yield (Defects)	~ 0.8%	~ 3%

Gas Flow Simulation



Cross-Section



Flow Velocity

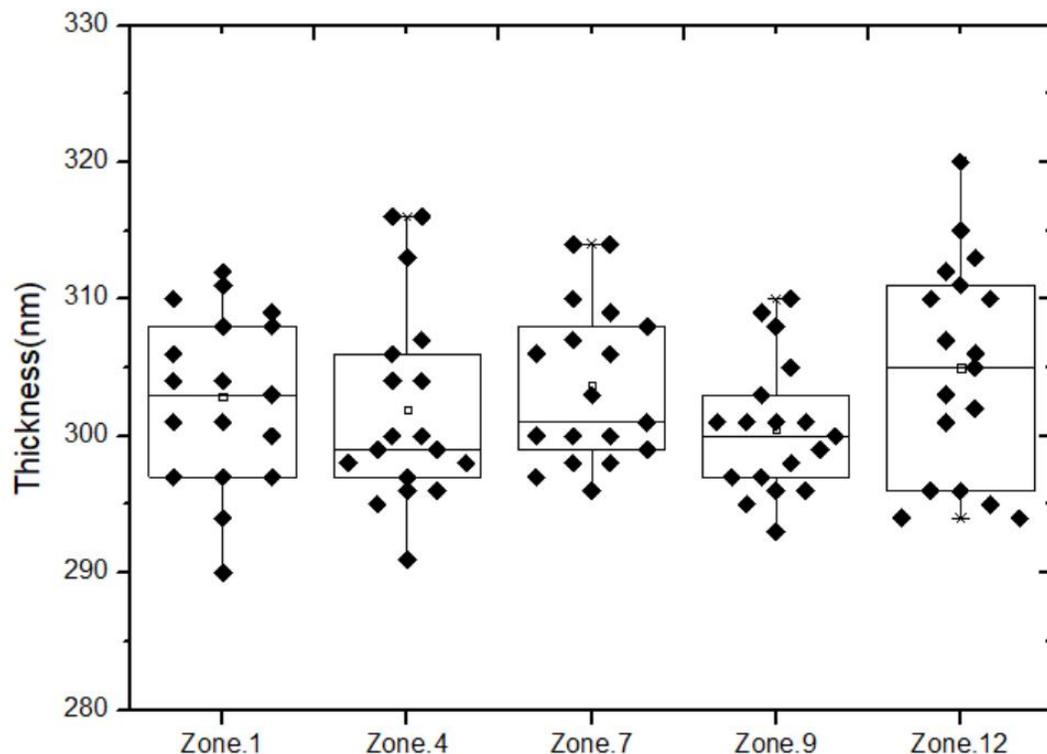


Concentration

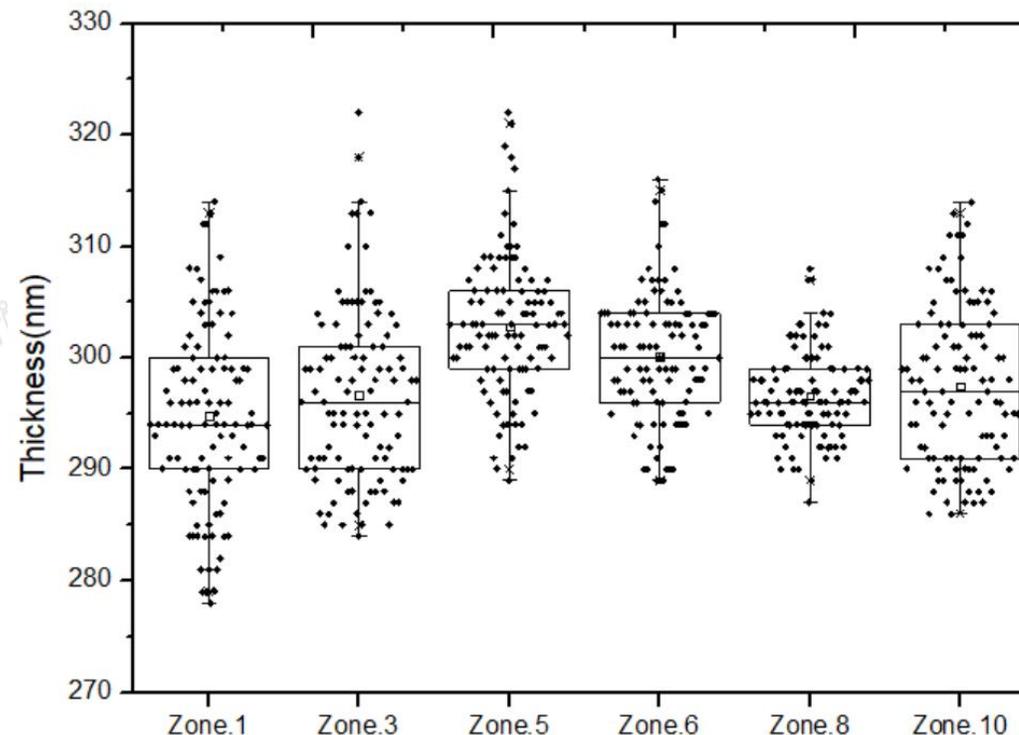
➤ Unique circular gas intake and uniform flow distribution system, to achieve **excellent gas flow and density uniformity**

Film Uniformity:

Half cell film uniformity



Full cell uniformity



➤ Excellent temp. and gas flow design, **ensured excellent film uniformity**

➤ **WIW/WTW/BTB: 3%3%3%**

2022:

- Boron Diffusion + LPCVD Poly
- High emitter resistance + paste development
- BCl₃ doping source development

Received: 22 May 2021 | Revised: 4 October 2021 | Accepted: 15 November 2021

DOI: 10.1002/pip.3519

APPLICATIONS

PROGRESS IN
PHOTOVOLTAICS WILEY

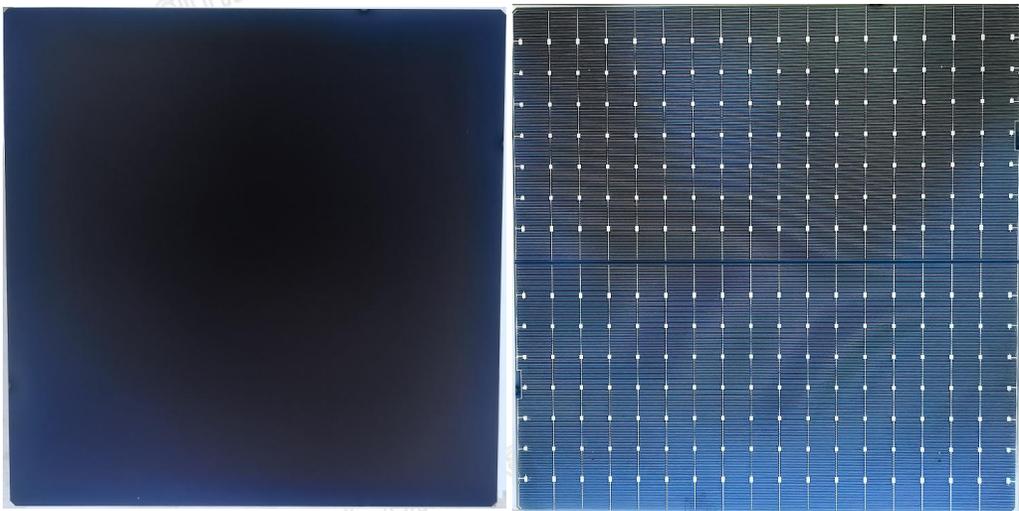
Unlocking the potential of boronsilicate glass passivation for industrial tunnel oxide passivated contact solar cells

Baochen Liao¹  | Jia Ge² | Xinyuan Wu³  | Qiang Wang¹ |
Reuben J. Yeo⁴  | Zheren Du⁵

3.2

Technical Progress of PECVD

6th Gen. PECVD Product Features



**Capacity
High**

(16.7% - 20%)↑

**Yield
High**

**Uniformity
Excellent**

6%→3%

(Ultimate Beauty for BC)

**Maint.
Easy**

**Unique Arc
Extinguishing design**

**Uptime
High**

Upto 98.6%

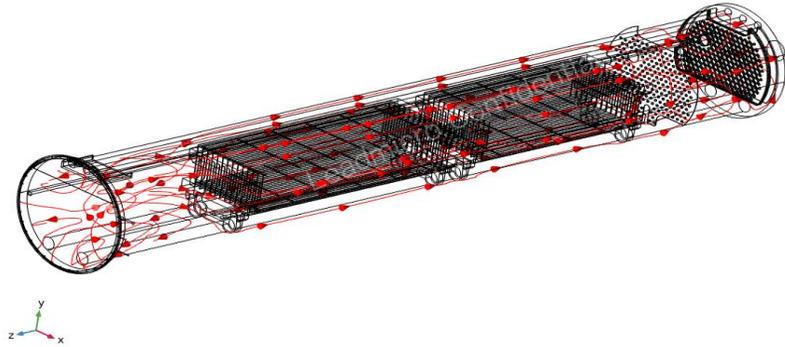
non-cooling

Electrode Maint. Tech.

Maint. time ↓600% (26H→<6H)

**Maturity
High**

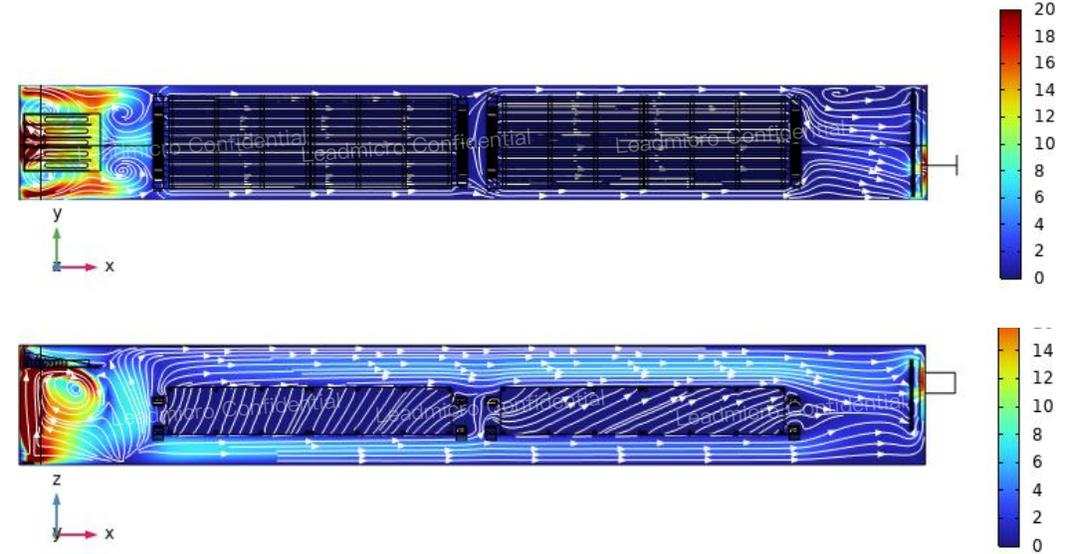
Physics Model



Gas Flow

m(1)=0.05

切面: Velocity magnitude (m/s) 多切面上的流线: Velocity field



Temperature Simulation

m(1)=0.05

切面: Temperature (degC)



m(1)=0.05

切面: Temperature (degC)

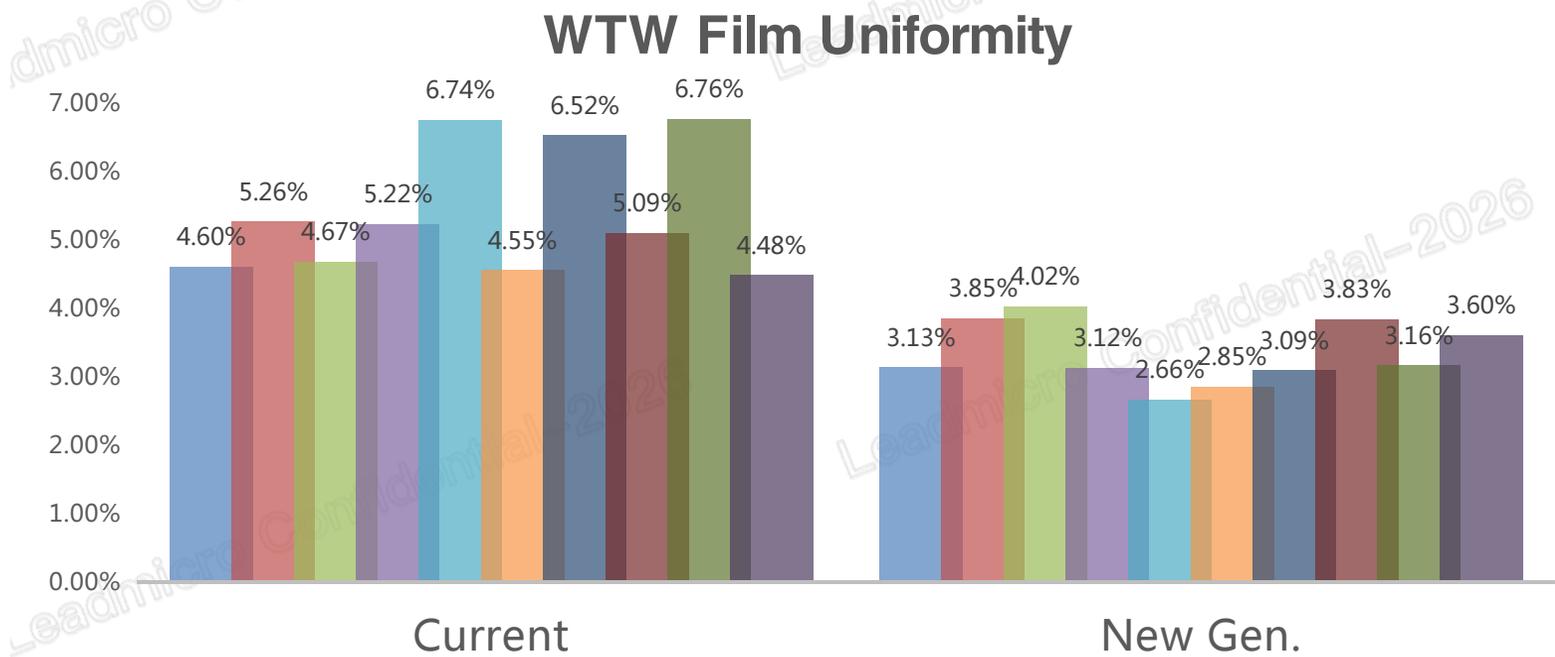
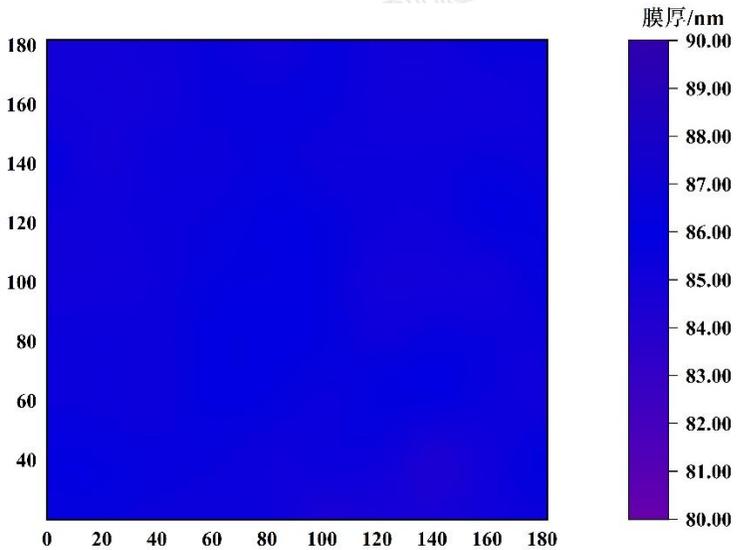
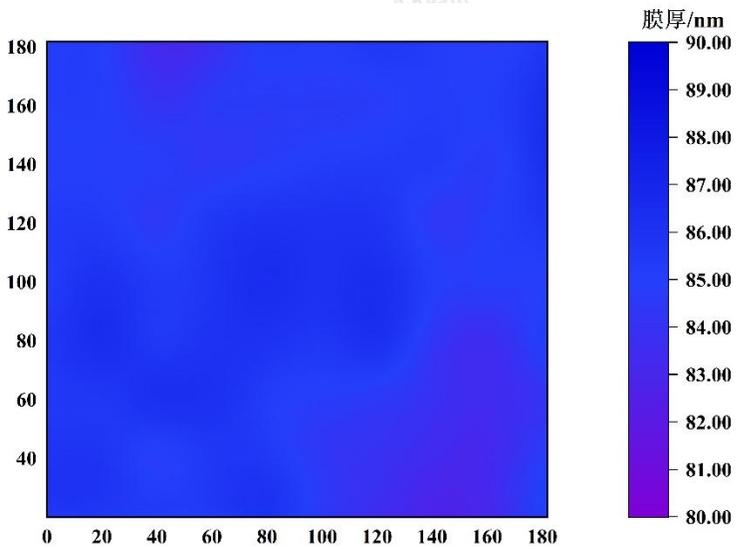


- Temperature simulation, to provide guidance to thermal compensation design
- Gas flow simulation, to provide guidance to gas flow design
- **Simulation + Actual Measurement :**

Excellent Film Uniformity

Confidential & Proprietary

Film Color improved Significantly



➤ Coloring: Significantly Improved

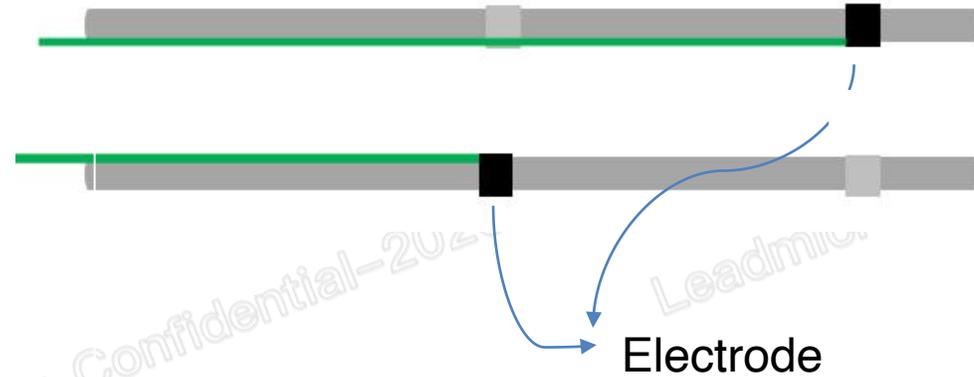
- ① WIW < 1.6% ;
- ② WTW 6.39% → 3.33% ;

**Leadmicro
Pioneer**

Non-cooling Electrode Components Maintenance Solution

Features :

- Removable Electrode online
- Removable electrode assembly online
- Unique Arc extinguishing design
- Impedance monitoring



Reduced **600%**
(from 26hrs to 6 hrs)



Reduced
87%



Reduced
83%



Greatly reduced
**Due to non-temp.
cooling**

2022: PEALD Al₂O₃ + LPCVD Poly

Received: 3 January 2022 | Revised: 18 June 2022 | Accepted: 27 June 2022

DOI: 10.1002/pip.3607

RESEARCH ARTICLE



Tube-type plasma-enhanced atomic layer deposition of aluminum oxide: Enabling record lab performance for the industry with demonstrated cell efficiencies >24%

Baochen Liao^{1,2} | Xinyuan Wu^{2,3} | Weiliang Wu⁴ | Changming Liu⁵ | Sheng Ma^{2,6} | Shaozhou Wang³ | Tong Xie³ | Qiang Wang¹ | Zheren Du⁷ | Wenzhong Shen⁶ | Xiang Li² | Weimin Li² | Bram Hoex³

2023: PECVD O₂ + PECVD n-Poly

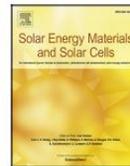
Solar Energy Materials & Solar Cells 257 (2023) 112396



Contents lists available at ScienceDirect

Solar Energy Materials and Solar Cells

journal homepage: www.elsevier.com/locate/solmat



24.7% industrial tunnel oxide passivated contact solar cells prepared through tube PECVD integrating with plasma-assisted oxygen oxidation and in-situ doped polysilicon

S. Ma^{a,b}, B. Liao^{c,d,***}, F.Y. Qiao^b, D. Ding^b, C. Gao^b, Z.P. Li^b, R. Tong^e, X.Y. Kong^{a,**}, W. Z. Shen^{b,*}



2023: PEALD SiO₂ + PECVD n-Poly

Received: 14 May 2022 | Revised: 18 August 2022 | Accepted: 16 September 2022

DOI: 10.1002/pip.3627

RESEARCH ARTICLE



Atomic scale controlled tunnel oxide enabled by a novel industrial tube-based PEALD technology with demonstrated commercial TOPCon cell efficiencies > 24%

Baochen Liao^{1,2} | Weiliang Wu³ | Reuben J. Yeo⁴ | Xinyuan Wu⁵ | Sheng Ma⁶ | Qiang Wang¹ | Yimao Wan⁷ | Xiaodong Su⁸ | Wenzhong Shen⁶ | Xiang Li² | Weimin Li² | Guoqiang Xing³ | Bram Hoex⁵

2024: PECVD NO₂ + PECVD n-Poly

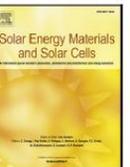
Solar Energy Materials & Solar Cells 275 (2024) 113024



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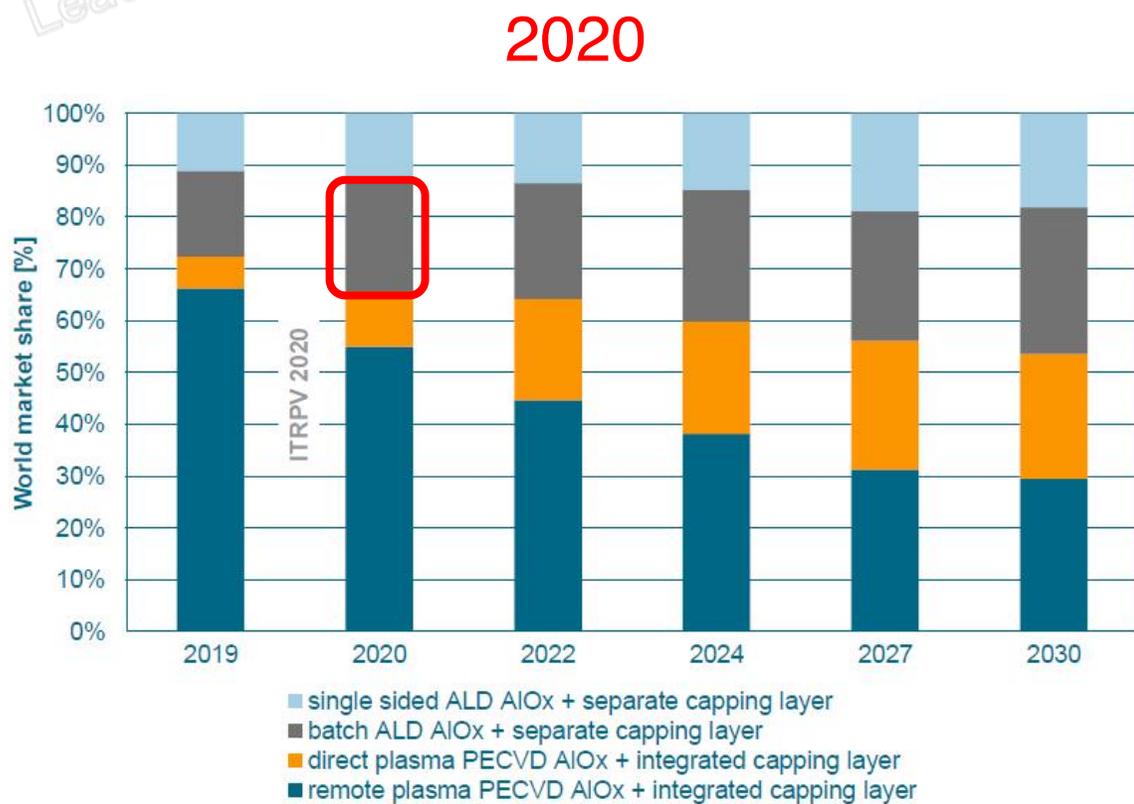
Improving the performance of industrial TOPCon solar cells through the insertion of intrinsic a-Si layer

S. Ma^{a,b}, D.X. Du^a, D. Ding^a, C. Gao^a, Z.P. Li^a, X.Y. Wu^c, S. Zou^d, X. Su^d, X.Y. Kong^b, B. Liao^{e,*}, W.Z. Shen^{a,**}

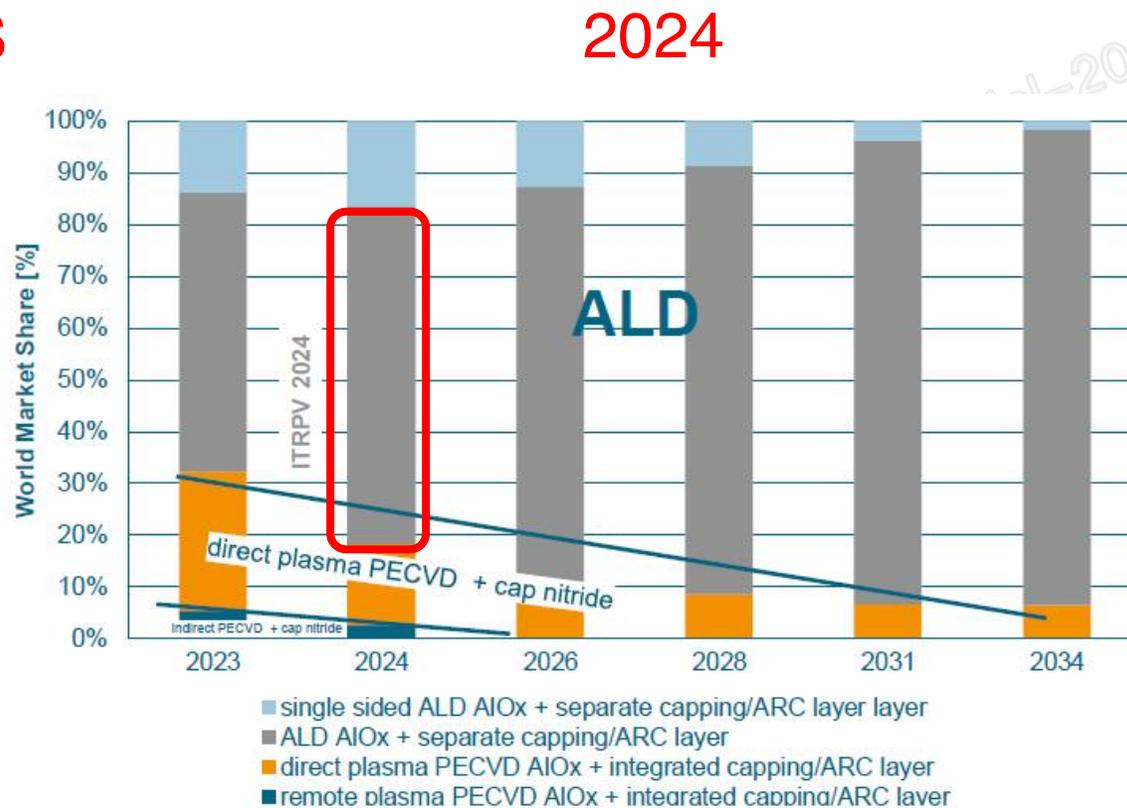
3.3

Technical Progress of ALD

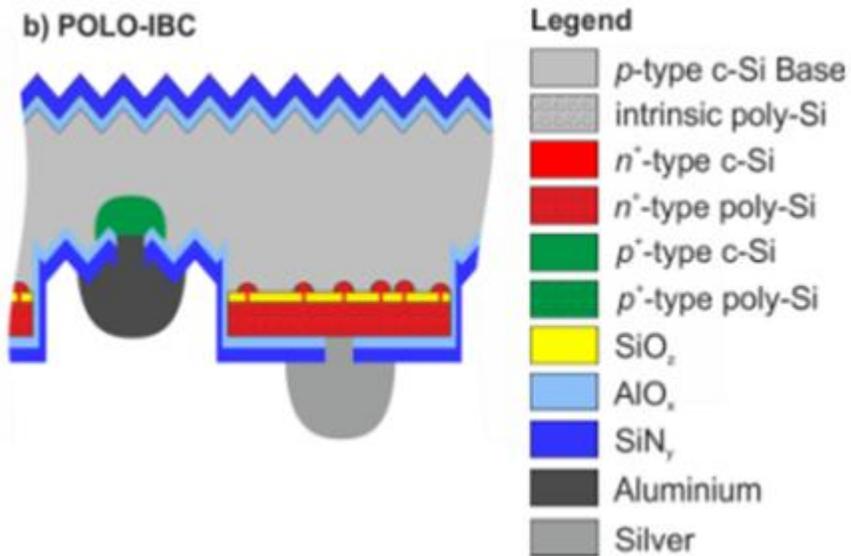
➤ Trend: AlOx deposition PERC/TOPCon



VS



➤ TBC, HPBC ALD Al_2O_3 New Requirement: double-side coating



Technology	Batch ALD Al_2O_3	In-line ALD	PECVD two-in-one
Efficiency	😊	😊	😞
Equipment Price	😊	😞	😊
Maintenance Period	😊	😞	😐
Operating Costs	😊	😞	😊
Double-side Coating	😊	😞	😞
Wrap-around	😐	😊	😐

F. Haase, *et al.*, 46th IEEE PVSC, 2019

Market Share Highest

Capacity Highest

Capacity High

Unique Design



**1.5XBoat Tech.
Capacity 50%↑**

**Each tube work/maint.
independently**

Uptime High

> 98%

Breakage Low

< 0.03%

Maint. Easy

Less powder

COO Low

Highly Automated

High-eff. Cell Tech.

Standard process for TOPCon, XBC, Perovskite, Tandem cells

Compatibility Good

Compatible with various rectangular size wafers

2012:

- Solved the bottlenecks for ALD Al₂O₃ from lab to PERC cell commercialization

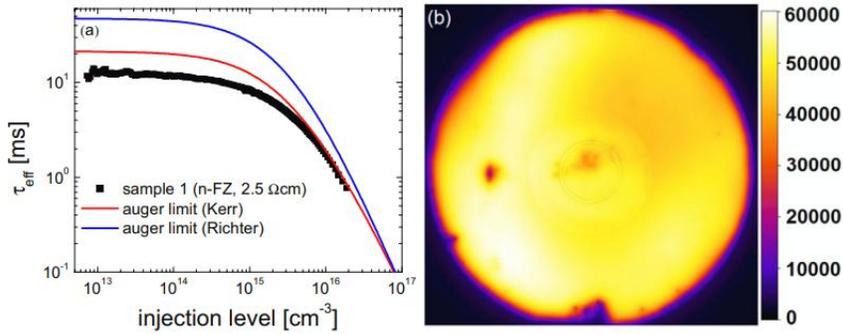


Table 3. A comparison of D_{it} and Q_f for Al₂O₃ under different anneal conditions and deposition methods.

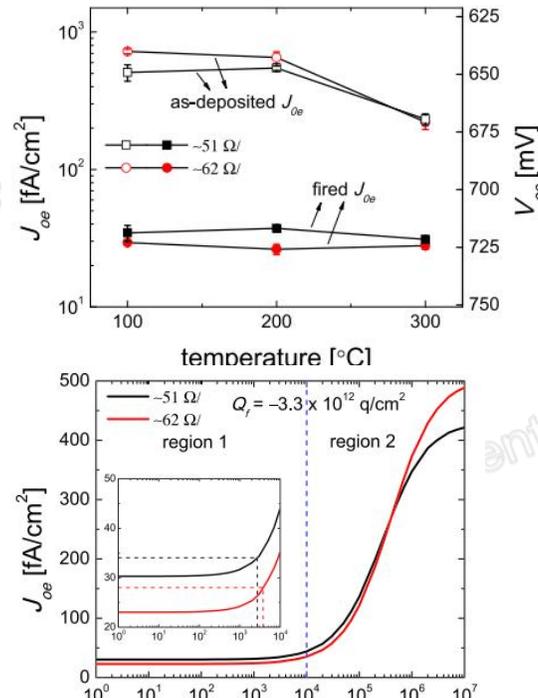
Deposition method	As-deposited		Anneal condition	Annealed/fired		Ref.
	D_{it} (cm ² eV ⁻¹)	Q_f (q/cm ²)		D_{it} (cm ² eV ⁻¹)	Q_f (q/cm ²)	
Plasma ALD	~10 ¹³	(1-3) × 10 ¹²	Annealed 400 °C, N ₂ , 10 min	1 × 10 ¹¹	5.8 × 10 ¹²	[9]
O ₃ -ALD	~10 ¹³	5.3 × 10 ¹²	Annealed 400 °C, N ₂ , 10 min	1 × 10 ¹¹	3.4 × 10 ¹²	[9]
H ₂ O-ALD	3 × 10 ¹¹	1.3 × 10 ¹¹	Annealed 400 °C, N ₂ , 10 min	1 × 10 ¹¹	2.4 × 10 ¹²	[9]
H ₂ O -ALD	3.3 × 10 ¹¹	1.4 × 10 ^{12a} 8.7 × 10 ^{11b}	Fired 800 °C (peak), air, 30 s	0.8 × 10 ^{11a}	3.3 × 10 ^{12a} 3.9 × 10 ^{12b}	This work

^a Obtained by using C-V method.

^b Obtained by using corona charger method.

2013:

- Proved ALD Al₂O₃ excellent surface passivation for boron surface
- Pave the way for today TOPCon's application



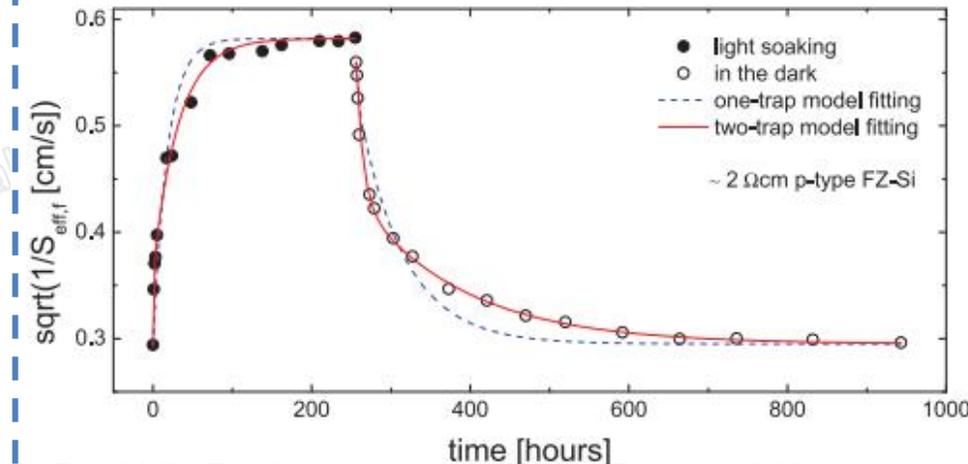
2013:

- Light-soaking mechanisms study

$$\frac{dn_i}{dt} = \frac{n_{0i} - n_i}{\tau_{ti}} - \frac{n_i}{\tau_{di}}$$

$$n_i(t) = \frac{n_{0i}\tau_{di}}{\tau_{ti} + \tau_{di}} \left(1 - \exp\left(-\left(\frac{1}{\tau_{ti}} + \frac{1}{\tau_{di}}\right)t\right) \right)$$

$$\sqrt{\frac{1}{s_{eff}(t)}} = a_0 + \sum_{i=1}^m a_i \left(1 - \exp\left(-\frac{t}{\tau_i}\right) \right)$$



3.4

Technical Progress of EPD & Laser

One-stop Compatibility

- TOPCon/0BB/Poly Finger/TBC
- Half/Third/Quarter cell tech.
- M10, G12R, G12
- Low long-term investment

Excellent Passivation

- **Chemical+Field effect + H passivation + thermal + light treatments**
- **Half cell > 5 W**
- **1/3 cell > 8 W**
- **1/4 cell > 10 W**

Conformality Excellent

- **Uneven cutting surface: ALD**

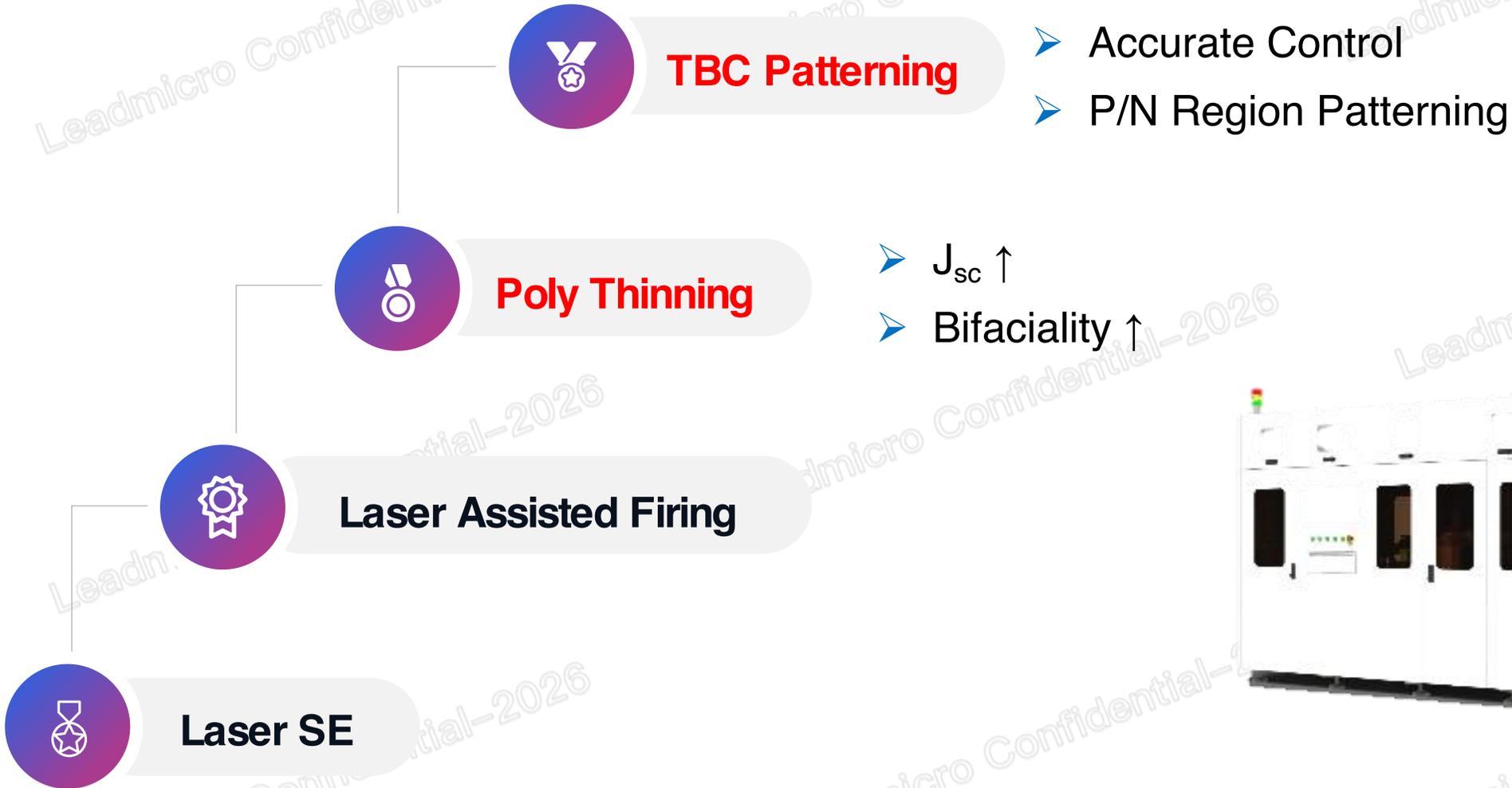
Capacity High

- **> 20000 pcs/hr (Full Cell)**

Stability Excellent

- **No freq. maint.**
- **Unique Live monitoring**

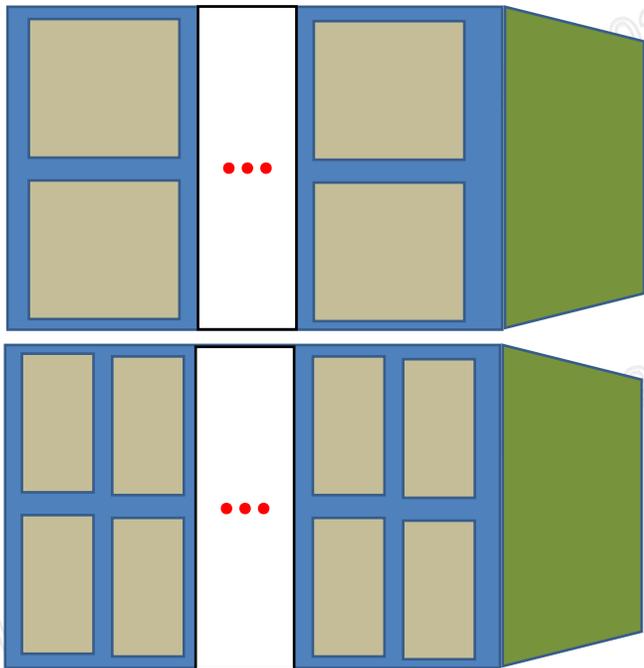




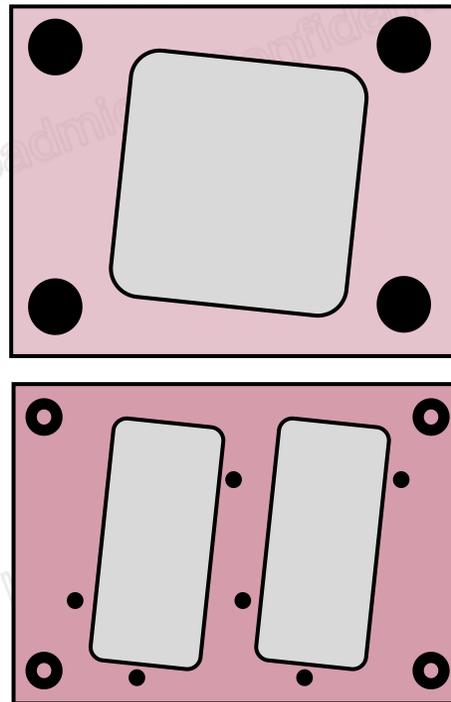
3.6

Half-cells Series Products for TBC

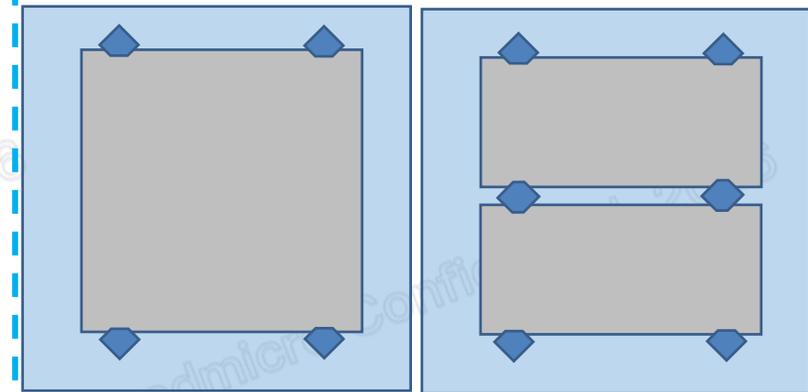
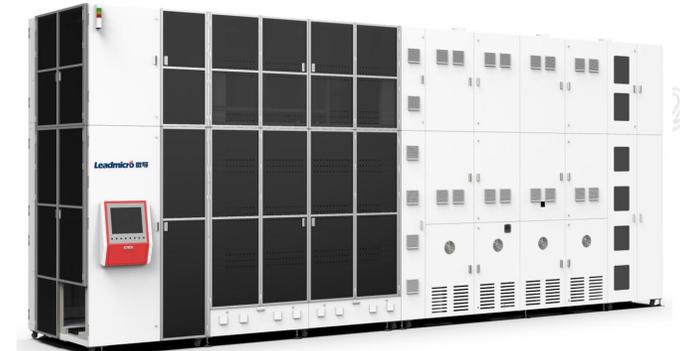
ALD KF20000S/D-H



PECVD ZR6000-H



Diffusion XH10000B-H



04

Company Introduction

One of the world largest ALD company

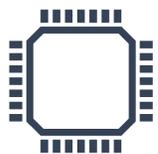
- World 1st IPO company with ALD core technology
- >2000 employee with > 36% R&D staff
- >20% R&D expenditure (> 20M USD in 2023)

No.1 ALD provider for PV industry in the world

- >3000 ALD reactors delivered
- >800 GW capacity cumulatively

No.1 ALD provider in SEMI industry in China

- >100 delivered/to be delivered ALD systems
- >300% rapid growth in 2023
- Only production proven supplier of 300mm ALD tool in China



半导体

Semiconductor



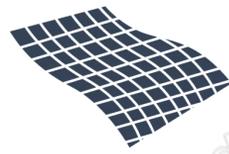
光伏

Photovoltaics



新能源

New Energy



新材料

New Material



产业化应用中心

IAC



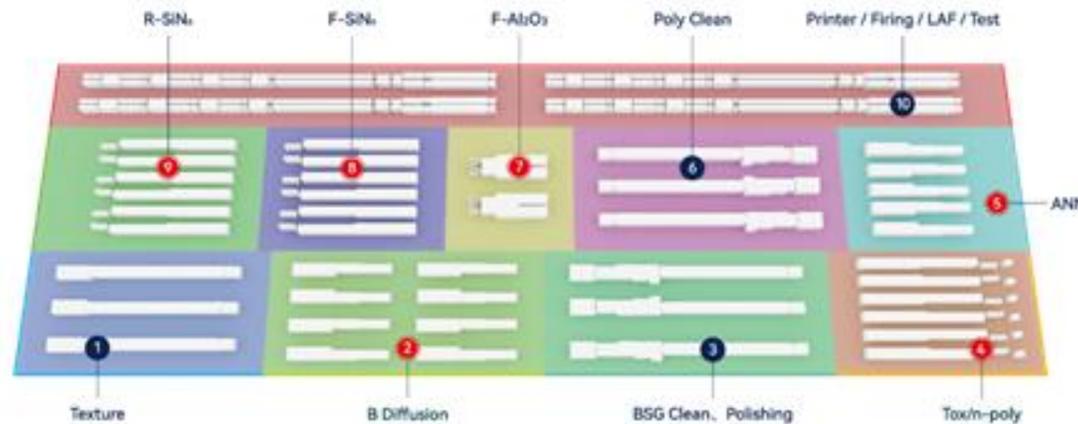
- The intellectual property across China, United States, continental Europe, Japan, Germany , India , South Korea and other countries and regions.
 - Patent Application > 760 ;
 - Granted IP > 230 ;
 - Proprietary Technologies > 3,000 ;
 - Global Registered Trademarks > 110.

The number of patent applications maintains a stable growth, with invention patent applications accounting for more than 60%.

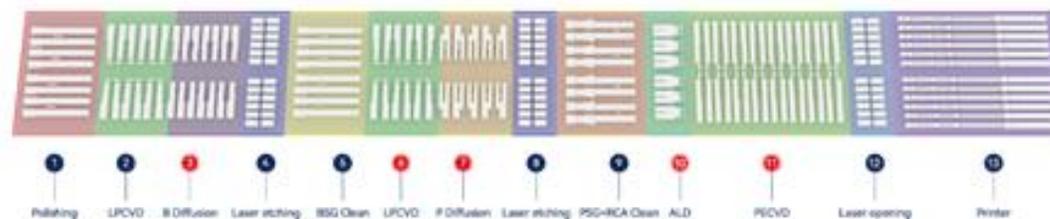
The IP conversion rate exceeds 80%, of which the industrialization rate of the company's effective invention patents exceeds 76%



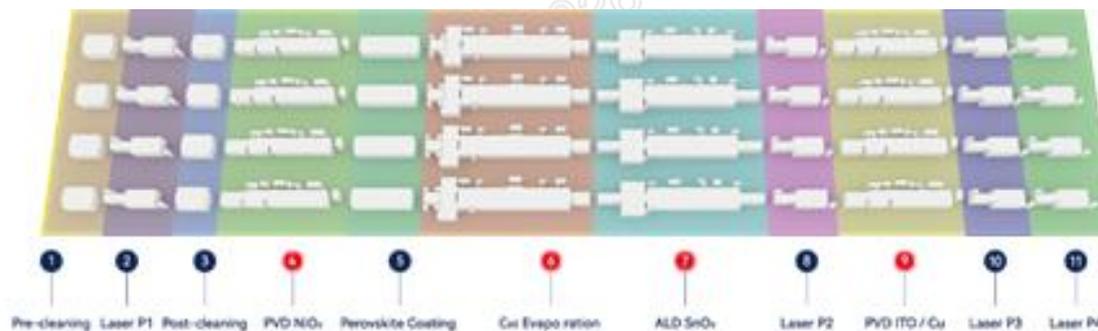
PE-TOPCon 4.0 Turnkey Solution



TBC Turnkey Solution



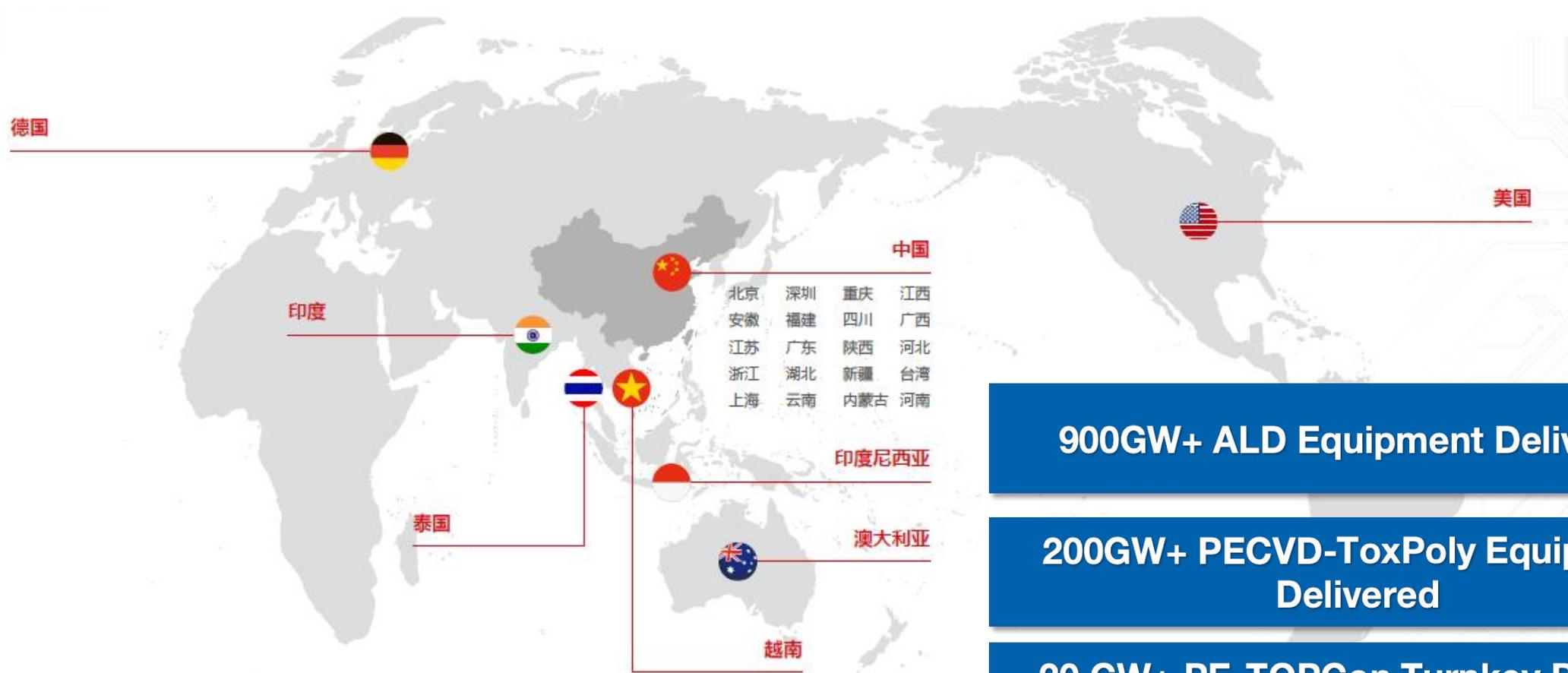
Perovskite/Tandem Turnkey Solution



KF	ZR	XH	JW	Laser	HY
KF20000S	ZR6000	XH10000	EPD40000		HY10000
					
Batch ALD/CVD	PECVD/PEALD	Diffusion Anneal Oxidation LPCVD	Edge Passivation	SE LAF Poly Thinning TBC Patterning Laser Cutting	In-line ALD/PEALD /PECVD
Al ₂ O ₃ , SiO ₂ , TiO ₂ , SnO _x , TCO	Al ₂ O ₃ , SiN _x , SiO ₂ , poly-Si (n&p), a-Si	O ₂ , BBr ₃ , BCl ₃ , POCl ₃ , poly-Si	Al ₂ O ₃		Al ₂ O ₃ , SiN _x , SiO ₂ , poly-Si (n&p), a-Si

HY	iSparol	SuiR MS	SuiR EVA	Laser
				
<p>In-line ALD/PEALD /PECVD</p>	<p>RTR Platform ALD</p>	<p>Magnetron Sputtering</p>	<p>Evaporation</p>	<p>P1-P4</p>
<p>Al_2O_3, SiN_x, SiO_2, poly-Si (n&p), a-Si</p>	<p>Al_2O_3, SiO_2, TiO_2, SnO_x</p>	<p>NiO_x, ITO, Cu/Ag</p>	<p>LiF, C60</p>	

Global Market Leader in ALD technology for PV industry

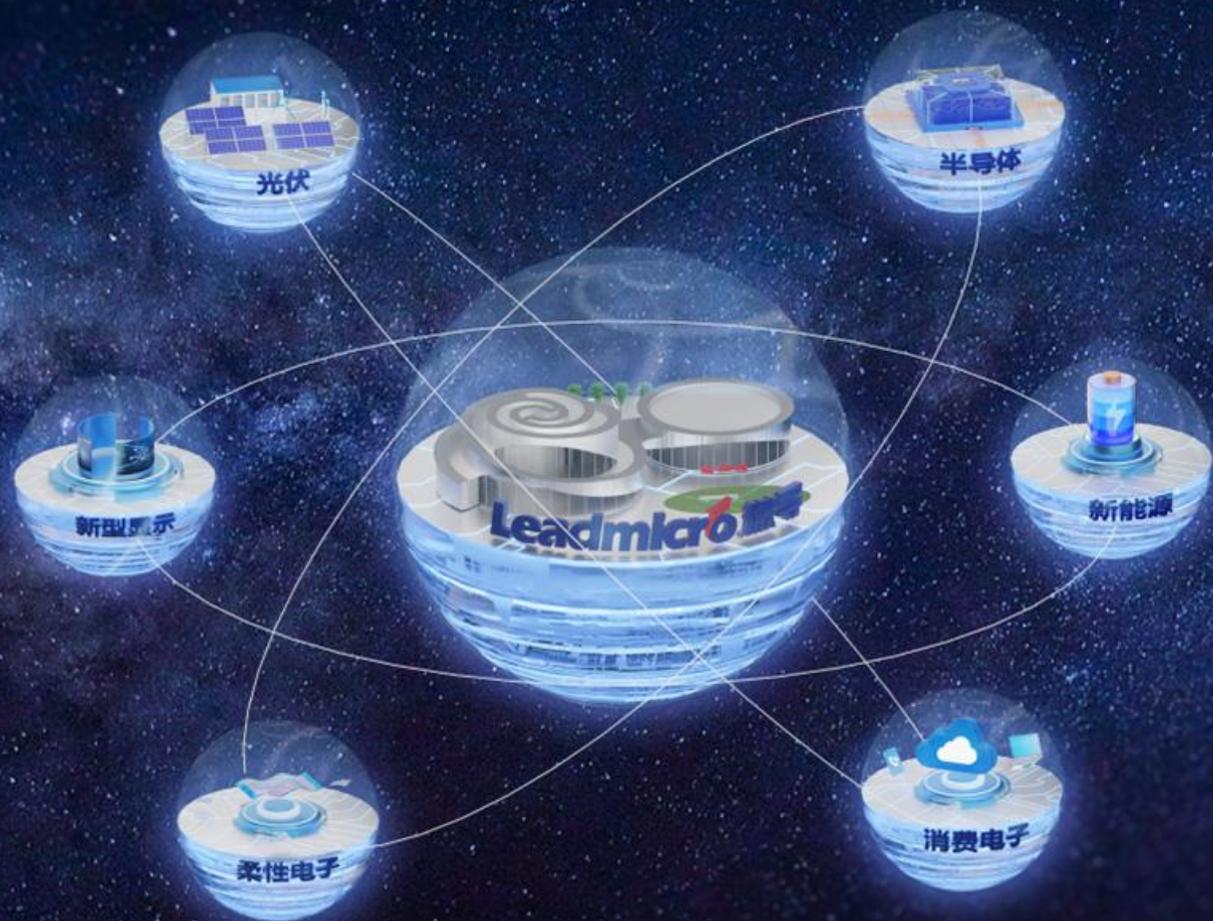


900GW+ ALD Equipment Delivered

200GW+ PECVD-ToxPoly Equipment Delivered

20 GW+ PE-TOPCon Turnkey Project Delivered

- Recent Progress of Cell Technologies
- TOPCon to TBC Solutions
 - ✓ LPCVD Route
 - ✓ LPCVD + PECVD Route
 - ✓ **PECVD Route (New Technology)**
- TBC Equipment Solutions
 - ✓ ALD: **1.5X Boat Tech., capacity improved \approx 50%**
 - ✓ LPCVD Route: **Like-PE loading**
 - ✓ PECVD: **capacity improved \approx 20%, uniformity 6% \rightarrow 3% (Extremely Beauty)**
 - ✓ EPD, Laser
- TBC Equipment Investment: from **360 to \sim 230 M/GW**



谢谢
THANK YOU